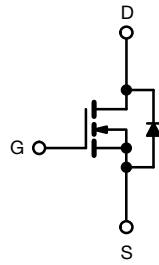
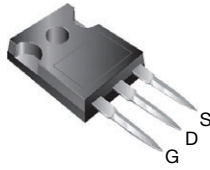


Power MOSFET

TO-247AC



N-Channel MOSFET

FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third Generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

PRODUCT SUMMARY

V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.60
Q_g (max.) (nC)	84	
Q_{gs} (nC)	8.4	
Q_{gd} (nC)	50	
Configuration	Single	

ORDERING INFORMATION

Package	TO-247AC
Lead (Pb)-free	IRFP448PbF

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	500	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current	I_D	V_{GS} at 10 V	A	
		$T_C = 25$ °C		11
		$T_C = 100$ °C	6.6	
Pulsed drain current ^a	I_{DM}	44	W/°C	
Linear derating factor		1.4		
Single pulse avalanche energy ^b	E_{AS}	550	mJ	
Repetitive avalanche current ^a	I_{AR}	11	A	
Repetitive avalanche energy ^a	E_{AR}	18	mJ	
Maximum power dissipation	P_D	180	W	
Peak diode recovery dV/dt ^c	dV/dt	3.5	V/ns	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature)	for 10 s	300 ^d		
Mounting torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 8.2$ mH, $R_g = 25$ Ω , $I_{AS} = 11$ A (see fig. 12)
- $I_{SD} \leq 11$ A, $dI/dt \leq 120$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
- 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.24	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.70	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.60	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 6.6\text{ A}^b$	-	-	0.60	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 6.6\text{ A}^b$	6.7	-	-	S
Dynamic						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	1900	-	pF
Output capacitance	C_{oss}		-	490	-	
Reverse transfer capacitance	C_{rss}		-	220	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 9.6\text{ A}$, $V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	84	nC
Gate-source charge	Q_{gs}		-	-	8.4	
Gate-drain charge	Q_{gd}		-	-	50	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 250\text{ V}$, $I_D = 9.6\text{ A}$, $R_G = 7.8\text{ }\Omega$, $R_D = 27\text{ }\Omega$, see fig. 10 ^b	-	18	-	ns
Rise time	t_r		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	62	-	
Fall time	t_f		-	32	-	
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact	-	5.0	-	nH
Internal source inductance	L_S		-	13	-	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode	-	-	11	A
Pulsed diode forward current ^a	I_{SM}		-	-	44	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 11\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	1.7	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 9.6\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	480	1100	ns
Body diode reverse recovery charge	Q_{rr}		-	5.2	12	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

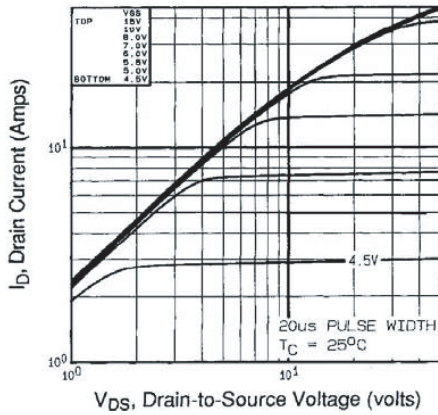


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

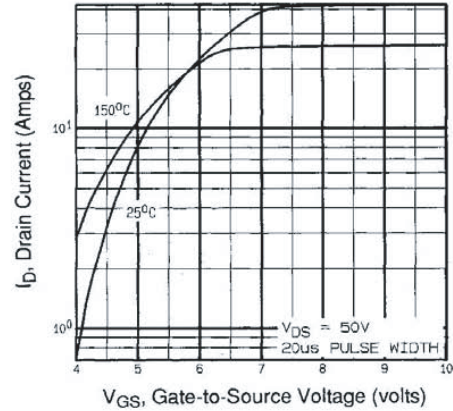


Fig. 3 - Typical Transfer Characteristics

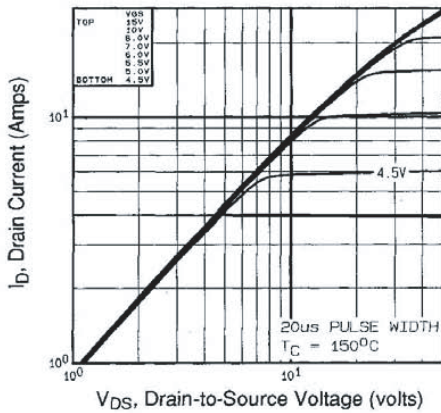


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

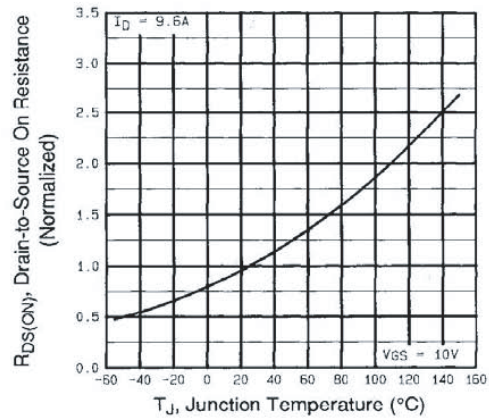


Fig. 4 - Normalized On-Resistance vs. Temperature

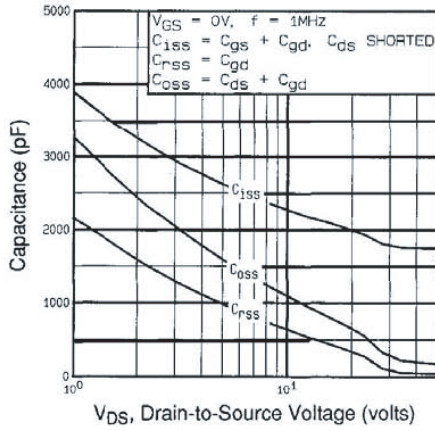


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

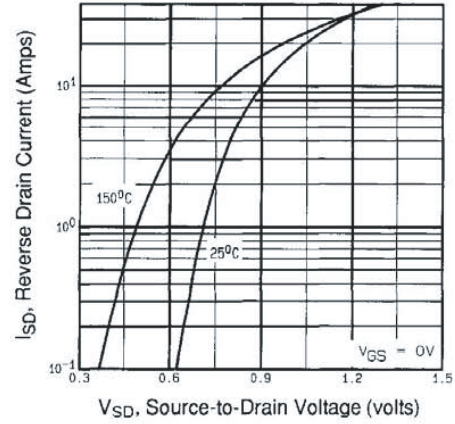


Fig. 7 - Typical Source-Drain Diode Forward Voltage

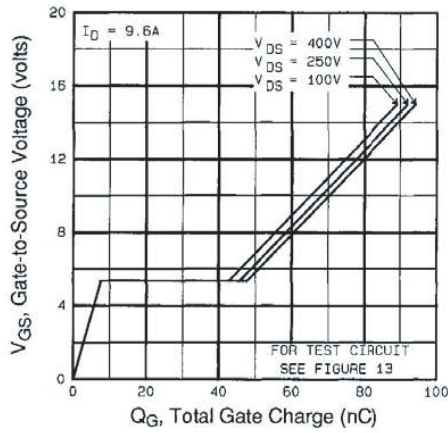


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

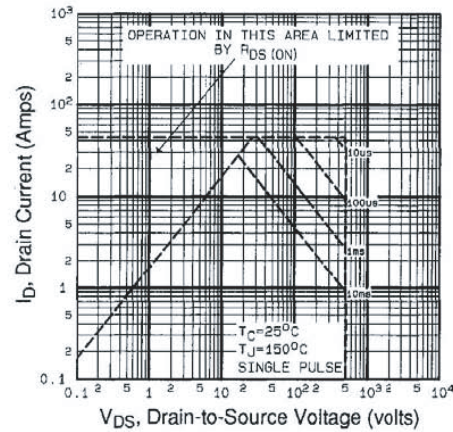


Fig. 8 - Maximum Safe Operating Area

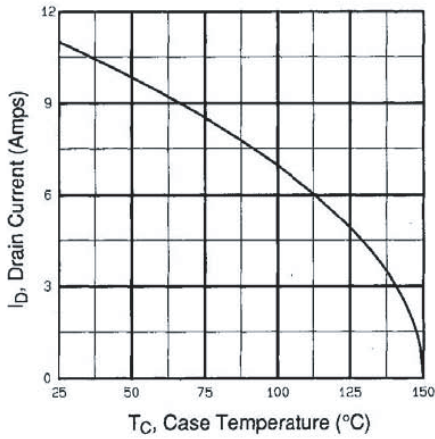


Fig. 9 - Maximum Drain Current vs. Case Temperature

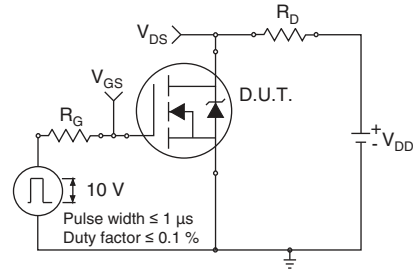


Fig. 10 - Switching Time Test Circuit



Fig. 11 - Switching Time Waveforms

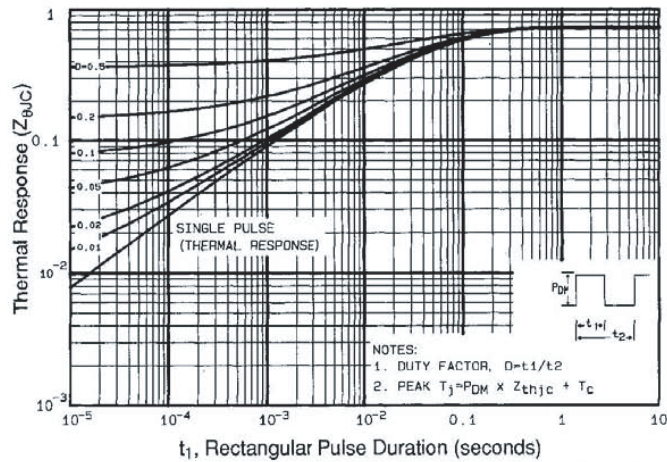


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

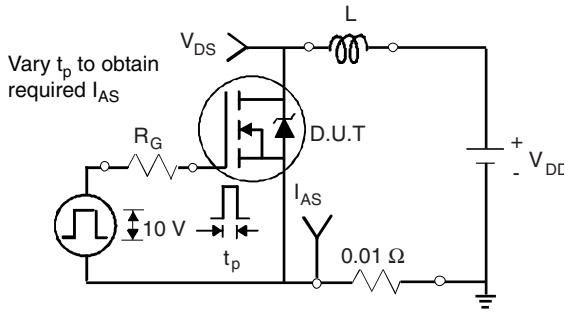


Fig. 13 - Unclamped Inductive Test Circuit

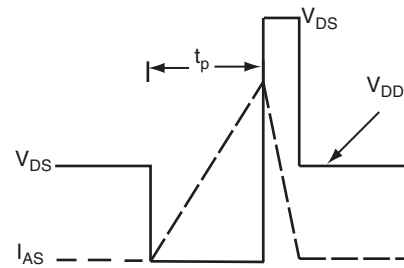


Fig. 14 - Unclamped Inductive Waveforms

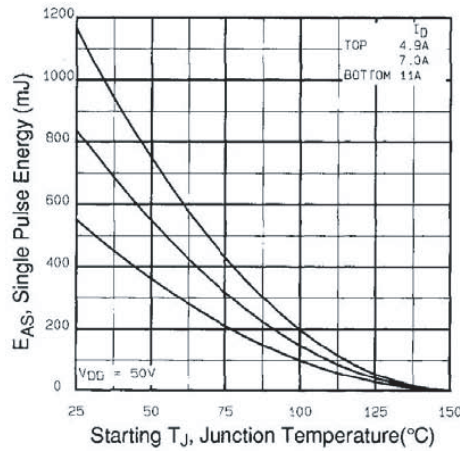


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

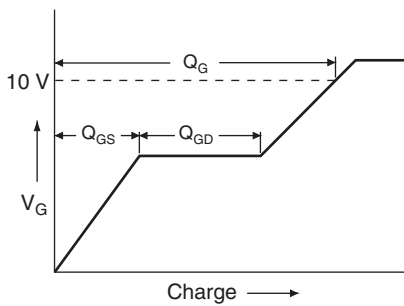


Fig. 16 - Basic Gate Charge Waveform

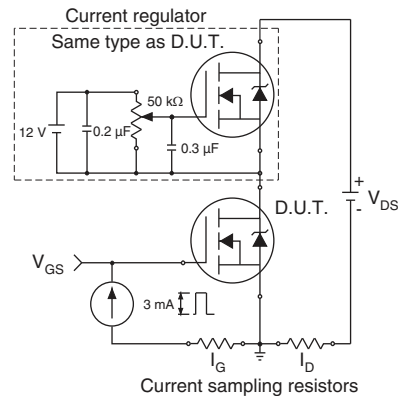
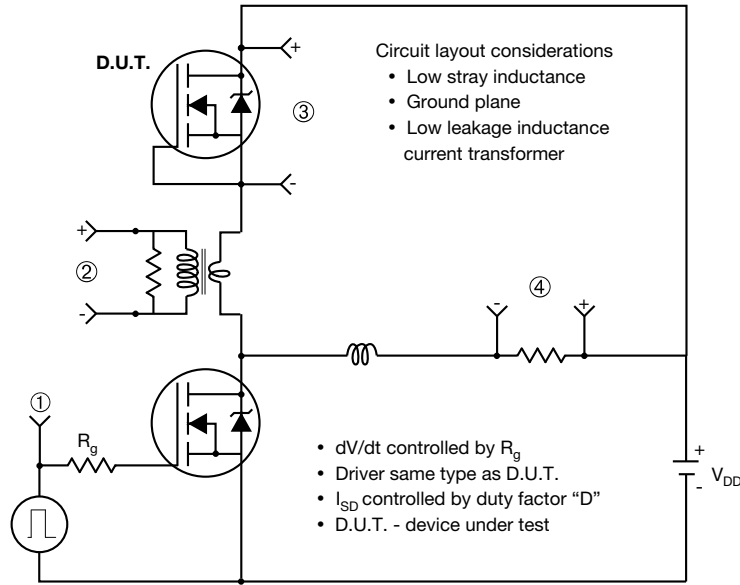


Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91229.



VERSION 2: FACILITY CODE = Y



DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

MILLIMETERS		
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

ECN: E22-0452-Rev. G, 31-Oct-2022
 DWG: 5971

- Notes**
- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
 - (2) Contour of slot optional
 - (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
 - (4) Thermal pad contour optional with dimensions D1 and E1
 - (5) Lead finish uncontrolled in L1
 - (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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